SKQ35P03AD

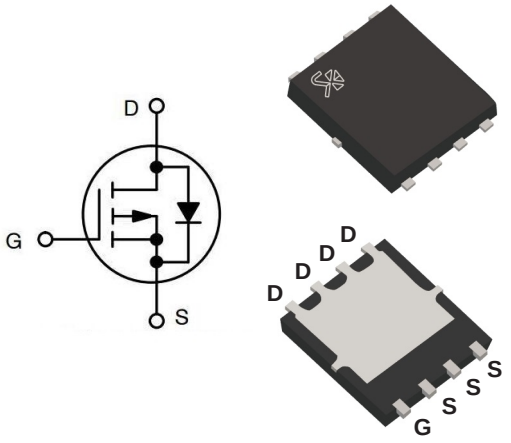
30V P-Channel MOSFET

Feature

- 30V P-Channel MOSFET High Dense Design.
- Ultra low On-Resistance.
- Reliable and Rugged.

Applications

- Power Management in Notebook Computer, and Portable Equipment and Battery Systems.



PDFN5060

Electrical Characteristics

Absolute Maximum Ratings (T_C=25°C unless otherwise noted)			
Parameter	**Symbol**	**Value**	**Unit**
Drain-Source Voltage	V_{DSS}	-30V	V
Gate-Source Voltage	V_{GSS}	±20V	V
Drain Current-Continuous @ T_C=25℃	I_D	-35	A
Drain Current-Pulsed	I_{DM}	-70	A
Operating Junction Temperature Range	T_J	-55 to 150°C	°C

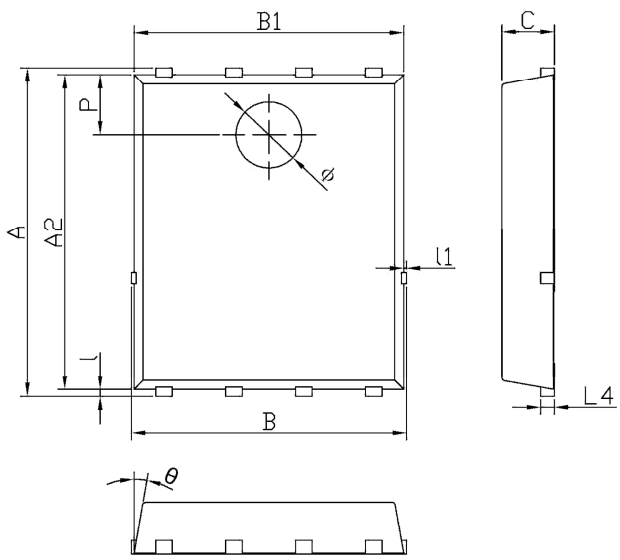
Electrical Characteristics(T_A=25°C unless otherwise noted)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
OFF CHARACTERISTIC						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V , ID=-250uA	-30	-	-	V
Drain-Source Leakage Current	I_{DSS}	V_{DS}=-24V, V_{GS}=0V, T_J=25°C	-	-	1	uA
Gate-Source Leakage Current	I_{GSS}	V_{GS}=±20V , V_{DS}=0V	-	-	±100	nA
ON CHARACTERISTIC						
Gate Threshold Voltage	$V_{GS(TH)}$	V_{GS}=V_{DS}, I_D=-250uA	-1.0	-	-2.5	V
Static Drain-Source On-Resistance	$R_{DS(ON)}$	V_{GS}=-10V , I_D=-6A	-	-	20	mΩ
		V_{GS}=-4.5V , I_D=-4A	-	-	32	
DYNAMIC CHARACTERISTICS						
Input Capacitance	Ciss	V_{DS}=-15V, V_{GS}=0V, f=1MHz	-	1345	-	pF
Output Capacitance	Coss		-	194	-	
Reverse Transfer Capacitance	Crss		-	158	-	
DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS						
Drain-Source Diode Forward Voltage	V_{SD}	V_{GS}=0V, Is=-1.0A	-	-	-1.2	V

Note: 1. The data tested by pulsed, pulse width≦300us, duty cycle ≦2%.
2. Rdson calculated by package type.

PDFN5060

Unit:mm



Dimensions In Millimeterer			
Symbol	MIN	TYP	MAX
A	5.90	6.00	6.10
a	3.91	4.01	4.11
A2	5.70	5.75	5.80
B	4.90	5.00	5.10
b	3.37	3.47	3.57
B1	4.80	4.90	5.00
C	0.90	0.95	1.00
L	0.35	0.40	0.45
l	0.06	0.13	0.20
L1	1.10	–	–
l1	–	–	0.10
L2	1.17	1.27	1.37
L4	0.21	0.26	0.34
L6	0.51	0.61	0.71
L7	0.51	0.61	0.71
P	1.00	1.10	1.20
θ	8°	10°	12°
ϕ	1.10	1.20	1.30